

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A method for manufacturing a semiconductor optical device includes: ~~step for~~ forming an epitaxial ~~growth-layer structure~~ containing at least an active layer which can emit light, ~~using of~~ a III-V group semiconductor material; ~~step for~~ forming an ~~insulation~~ insulating layer over the epitaxial ~~growth-layer structure~~, which ~~can prevent~~ prevents the V group element from escaping from the epitaxial structure during heat treatment; ~~step for applying heat treatment to~~ treating the epitaxial ~~growth-layer structure~~ at a temperature of at least 800 degree- degrees C or more; and ~~step for~~ removing the ~~insulation~~ insulating layer, thereby ~~remarkably~~ enhancing the reliability of the device.